

In the Specification:

Please amend the paragraph beginning on page 1, line 16, as follows:

In general, the most widely used gate electrode in semiconductor devices is a doped polycrystalline ~~silicene~~ silicon. As higher integration of semiconductor devices are being developed, metallic layers of titanium and tungsten are also widely used.

Please amend the paragraph beginning on page 1, line 21, as follows:

While the gate electrode using polycrystalline ~~silicene~~ silicon has the advantage of ensuring stability of the process, its high specific resistance causes reduction of the design rule, thus hindering improvement of the operational speed.

Please amend the paragraph beginning on page 2, line 15, as follows:

As shown in Figure 1a, a gate oxide 1a, a ~~poly~~ poly silicon layer 2, a tungsten nitride layer 3, a tungsten layer 4, a nitride layer 5 and an anti-reflection layer 6 are sequentially deposited on a semiconductor substrate 1.

Please amend the paragraph beginning on page 5, line 19, as follows:

Preferably, the etching prevention layer has a thickness ranging from about 50 to about ~~000Å~~ 1000Å.